



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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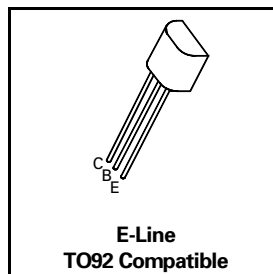
NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTORS

BCX38A/B/C

ISSUE 1 – MARCH 94

FEATURES

- * 60 Volt V_{CE0}
- * Gain of 10K at $I_C=0.5$ Amp
- * $P_{tot}=1$ Watt



ABSOLUTE MAXIMUM RATINGS.

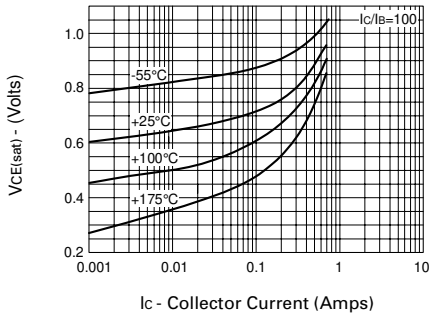
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	800	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

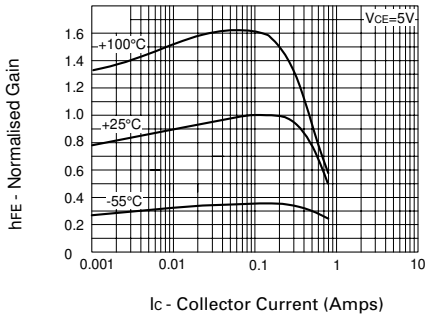
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80			V	$I_C=10\mu\text{A}, I_E=0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	60			V	$I_C=10\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=10\mu\text{A}, I_C=0$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=60\text{V}, I_E=0$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=8\text{V}, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1.25	V	$I_C=800\text{mA}, I_B=8\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			1.8	V	$I_C=800\text{mA}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	BCX38A	h_{FE}	500 1000			$I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=500\text{mA}, V_{CE}=5\text{V}^*$
	BCX38B		2000 4000			$I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=500\text{mA}, V_{CE}=5\text{V}^*$
	BCX38C		5000 10000			$I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=500\text{mA}, V_{CE}=5\text{V}^*$

BCX38A/B/C

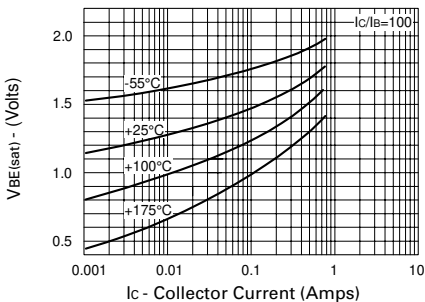
TYPICAL CHARACTERISTICS



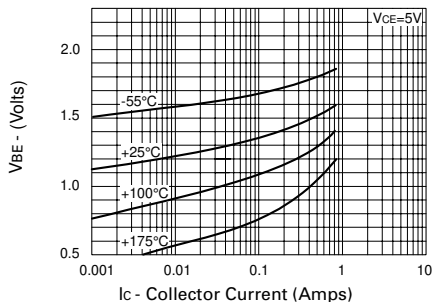
VCE(sat) v IC



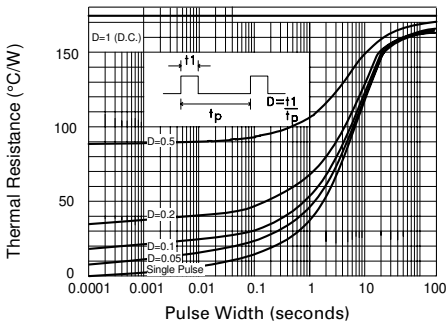
hFE v IC



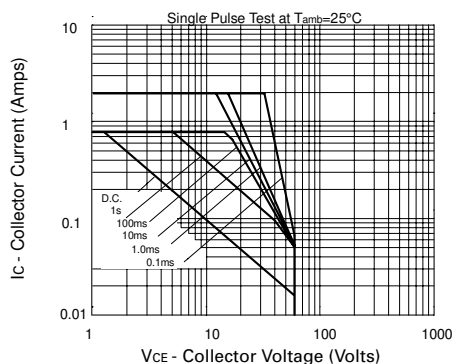
VBE(sat) v IC



VBE(on) v IC

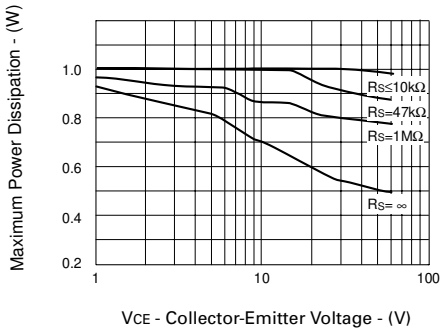


Maximum transient thermal impedance



Safe Operating Area

BCX38A/B/C



The maximum permissible operational temperature can be obtained using the equation:

$$T_{amb(max)} = \frac{Power(max) - Power(actual)}{0.0057} + 25^\circ C$$

$T_{amb(max)}$ = Maximum operating ambient temperature

Power (max) = Maximum power dissipation figure, for a given V_{CE} and source resistance (R_S)

Power (actual) = Actual power dissipation in users circuit